Markus Pristovsek

List of Publications by Year
in descending order

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135	2,287	26	37
papers	citations	h-index	g-index

249298

371746

135	135	135	1902
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Defect characterization of {101Â¯3} GaN by electron microscopy. Journal of Applied Physics, 2022, 131, .	1.1	5
2	Interplay of sidewall damage and light extraction efficiency of micro-LEDs. Optics Letters, 2022, 47, 2250.	1.7	15
3	The stability of graphene and boron nitride for III-nitride epitaxy and post-growth exfoliation. Chemical Science, 2021, 12, 7713-7719.	3.7	24
4	X-ray characterisation of the basal stacking fault densities of (112Ì„2) GaN. CrystEngComm, 2021, 23, 6059-6069.	1.3	4
5	Strain-induced yellow to blue emission tailoring of axial InGaN/GaN quantum wells in GaN nanorods synthesized by nanoimprint lithography. Scientific Reports, 2021, 11, 6754.	1.6	7
6	The Effect of Interface Diffusion on Raman Spectra of Wurtzite Short-Period GaN/AlN Superlattices. Nanomaterials, 2021, 11, 2396.	1.9	5
7	Scalable synthesis of multilayer h-BN on AlN by metalorganic vapor phase epitaxy: nucleation and growth mechanism. 2D Materials, 2020, 7, 015004.	2.0	17
8	Indium incorporation and optical properties of polar, semipolar and nonpolar InAlN. Semiconductor Science and Technology, 2020, 35, 035004.	1.0	11
9	Increasing the Luminescence Efficiency of Long-Wavelength (<mml:math) Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf 50 447 Td (xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mrow>	1.5	2
10	Epitaxial Combination of Two-Dimensional Hexagonal Boron Nitride with Single-Crystalline Diamond Substrate. ACS Applied Materials & Interfaces, 2020, 12, 46466-46475.	4.0	13
11	Pulsed-flow growth of polar, semipolar and nonpolar AlGaN. Journal of Materials Chemistry C, 2020, 8, 8668-8675.	2.7	9
12	Limitation of simple np-n tunnel junction based LEDs grown by metal-organic vapor phase epitaxy. Semiconductor Science and Technology, 2020, 35, 115005.	1.0	4
13	Wurtzite AlP y N1âˆ’y : a new III-V compound semiconductor lattice-matched to GaN (0001). Applied Physics Express, 2020, 13, 111001.	1.1	3
14	Untwinned semipolar (101Ì…3) Al_{<i>x</i>}Ga_{1-<i>x</i>}N layers grown on m-plane sapphire. Semiconductor Science and Technology, 2019, 34, 125012.	1.0	4
15	Monolithic integration of tricolor micro-LEDs and color mixing investigation by analog and digital dimming. Japanese Journal of Applied Physics, 2019, 58, SCCC06.	0.8	19
16	Controlling the orientations of directional sputtered non- and semi-polar GaN/AlN layers. Japanese Journal of Applied Physics, 2019, 58, SC1044.	0.8	3
17	Corrigendum to â€œMorphological study of InGaN on GaN substrate by supersaturationâ€•[J. Cryst. Growth 508 (2019) 58â€“65]. Journal of Crystal Growth, 2019, 514, 13.	0.7	1
18	Ammonia decomposition and reaction by high-resolution mass spectrometry for group III â€“ Nitride epitaxial growth. Journal of Crystal Growth, 2019, 516, 63-66.	0.7	8

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19	Effect of substrate misorientation on the concentration of impurities and surface morphology of an epitaxial GaN layer on N-polar GaN substrate by MOVPE. Journal of Crystal Growth, 2019, 512, 78-83.	0.7	13
20	Nonpolar m-plane <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si3.gif" overflow="scroll"><mml:mrow><mml:msub><mml:mrow><mml:mtext>Al</mml:mtext></mml:mrow><mml:mrow><mml:mi>x</mml:mi layers grown on m-plane sapphire by MOVPE. Journal of Crystal Growth, 2019, 512, 100-104.	0.7	11
21	Aluminium incorporation in polar, semi- and non-polar AlGaN layers: a comparative study of x-ray diffraction and optical properties. Scientific Reports, 2019, 9, 15802.	1.6	12
22	How to obtain metal-polar untwinned high-quality (1â€¯0â€¯â€'1â€¯3) GaN on m-plane sapphire. Journal of Crystal Growth, 2019, 507, 205-208.	0.7	16
23	Morphological study of InGaN on GaN substrate by supersaturation. Journal of Crystal Growth, 2019, 508, 58-65.	0.7	10
24	Effect of gas phase temperature on InGaN grown by metalorganic vapor phase epitaxy. Journal of Crystal Growth, 2019, 509, 50-53.	0.7	4
25	Growth of hexagonal boron nitride on sapphire substrate by pulsed-mode metalorganic vapor phase epitaxy. Journal of Crystal Growth, 2018, 482, 1-8.	0.7	46
26	What is red? On the chromaticity of orange-red InGaN/GaN based LEDs. Journal of Applied Physics, 2018, 124, .	1.1	27
27	Comparing high-purity <i>c</i>- and <i>m</i>-plane GaN layers for Schottky barrier diodes grown homoepitaxially by metalorganic vapor phase epitaxy. Japanese Journal of Applied Physics, 2018, 57, 105501.	0.8	5
28	MOVPE growth and high-temperature annealing of (101Â¯0) AlN layers on (101Â¯0) sapphire. Journal of Crystal Growth, 2018, 502, 14-18.	0.7	14
29	Simultaneous Growth of Various InGaN/GaN Coreâ€Shell Microstructures for Color Tunable Device Applications. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1800361.	0.8	14
30	High-temperature thermal annealing of nonpolar (1 0<mml:math) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 327 Td (xmlns:mml="http://www		

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37	Radiative recombination mechanisms in polar and non-polar InGaN/GaN quantum well LED structures. Applied Physics Letters, 2016, 109, .	1.5	41
38	Breakdown of the green gap in (0001) InGaN LEDs. , 2016, , .		0
39	Comparative study of (0001) and $(11ar{2}2)$ InGaN based light emitting diodes. Japanese Journal of Applied Physics, 2016, 55, 05FJ10.	0.8	7
40	The impact of the surface on step-bunching and diffusion of Ga on GaAs (001) in metal-organic vapour phase epitaxy. Materials Research Express, 2016, 3, 075902.	0.8	4
41	MOVPE growth and indium incorporation of polar, semipolar (112) and (201)â€‰InGaN. Physica Status Solidi (B): Basic Research, 2016, 253, 93-98.	0.7	5
42	Toward defectâ€free semiâ€polar GaN templates on preâ€structured sapphire (Phys. Status Solidi B 5/2016). Physica Status Solidi (B): Basic Research, 2016, 253, 1024-1024.	0.7	0
43	Structural and optical properties of (112Ì…2) InGaN quantum wells compared to (0001) and (112Ì…0). Semiconductor Science and Technology, 2016, 31, 085007.	1.0	5
44	Determination of axial and lateral exciton diffusion length in GaN by electron energy dependent cathodoluminescence. Journal of Applied Physics, 2016, 120, .	1.1	14
45	Optimizing GaN () heteroâ€epitaxial templates grown on () sapphire. Physica Status Solidi (B): Basic Research, 2016, 253, 61-66.	0.7	19
46	Development of semipolar (11-22) LEDs on GaN templates. Proceedings of SPIE, 2016, , .	0.8	8
47	Origin of faceted surface hillocks on semi-polar <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si0007.gif" overflow="scroll"><mml:mo stretchy="false">(</mml:mo><mml:mrow><mml:mn>1</mml:mn><mml:mspace width=".16em") Tj ETQq1 1 0.784314 rgBT /Overloc template	0.7	8
48	Effect of heterostructure design on carrier injection and emission characteristics of 295â€‰nm light emitting diodes. Journal of Applied Physics, 2015, 117, .	1.1	32
49	Low defect large area semiâ€polar (112) GaN grown on patterned (113) silicon. Physica Status Solidi (B): Basic Research, 2015, 252, 1104-1108.	0.7	16
50	Surface and crystal structure of nitridated sapphire substrates and their effect on polar InN layers. Applied Surface Science, 2014, 307, 461-467.	3.1	11
51	Role of nitridation on polarity and growth of InN by metalâ€“organic vapor phase epitaxy. Journal of Crystal Growth, 2013, 376, 17-22.	0.7	5
52	Energetics of Quantum Dot Formation and Relaxation of InGaAs on GaAs(001). Japanese Journal of Applied Physics, 2013, 52, 041201.	0.8	7
53	Structural and optical properties of semipolar AlGaN grown on sapphire by metalâ€“organic vapor phase epitaxy. Journal of Crystal Growth, 2013, 367, 42-47.	0.7	40
54	Growth mode transition and relaxation of thin InGaN layers on GaN (0001). Journal of Crystal Growth, 2013, 372, 65-72.	0.7	19

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55	Wavelength limits for InGaN quantum wells on GaN. Applied Physics Letters, 2013, 102, .	1.5	12
56	Polarity determination of polar and semipolar (112Â¯2)â€‰InN and GaN layers by valence band photoemission spectroscopy. Journal of Applied Physics, 2013, 114, .	1.1	30
57	Surface Transitions During InGaN Growth on GaN(0001) in Metalâ€“Organic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2013, 52, 08JB23.	0.8	6
58	Nucleation and Coalescence of Indium Rich InGaN Layers on Nitridated Sapphire in Metalâ€“Organic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2013, 52, 08JD03.	0.8	4
59	Indium incorporation efficiency and critical layer thickness of (202Â¯1) InGaN layers on GaN. Applied Physics Letters, 2012, 101, .	1.5	21
60	<i>In situ</i>access to the dielectric anisotropy of buried III-V/Si(100) heterointerfaces. Physical Review B, 2012, 86, .	1.1	19
61	Growth and characterizations of semipolar (112Â¯2) InN. Journal of Applied Physics, 2012, 112, .	1.1	26
62	Interface and surface dielectric anisotropies of GaP/Si(100). , 2012, , .		0
63	MOVPE growth of semipolar <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si0007.gif" overflow="scroll"><mml:mo stretchy="false">(</mml:mo><mml:mn>11</mml:mn><mml:mover) Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf 50 427 Td (accent="tr	0.7	45
64	Topography of <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si0005.gif" overflow="scroll"><mml:mo stretchy="false">(</mml:mo><mml:mn>20</mml:mn><mml:mover) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 3 phase epitaxy. Journal of Crystal Growth, 2012, 356, 70-74.	0.7	31
65	Influence of group III and group V partial pressures on the size and density of InGaN quantum dots in MOVPE. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 2487-2491.	0.8	4
66	Surface diffusion and layer morphology of ((112Â¯2)) GaN grown by metal-organic vapor phase epitaxy. Journal of Applied Physics, 2012, 111, .	1.1	48
67	Comparison study of Nâ€•and Inâ€polar {0001} InN layers grown by MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 977-981.	0.8	6
68	Single phase <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si0012.gif" overflow="scroll"><mml:mo stretchy="false">{</mml:mo><mml:mn>1</mml:mn><mml:mspace width="0.25em" /><mml:mn>1</mml:mn><mml:mspace width="0.25em" /><mml:mover accent="true"><mml:mrow><mml:mn>2</mml:mn></mml:mrow><mml:mrow><mml:mo>Â¯</mml:mo></mml:mrow></mml:mover><m width="0.25em" /><mml:mn>2</mml:mn><mml:mo stretchy="false">}</mml:mo></mml:math> GaN on <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" al. Journal of Crystal Growth, 2011, 331	0.7	23
69	Growth mechanism of InGaN quantum dots during metalorganic vapor phase epitaxy. Journal of Crystal Growth, 2011, 334, 40-45.	0.7	14
70	Crystal orientation of GaN layers on (101 0) m -plane sapphire. Physica Status Solidi (B): Basic Research, 2011, 248, 583-587.	0.7	42
71	High aluminium content and high growth rates of AlGaN in a close-coupled showerhead MOVPE reactor. Journal of Crystal Growth, 2011, 315, 229-232.	0.7	30
72	Surface transition induced island formation on thin strained InGaN layers on GaN (0001) in metal-organic vapour phase epitaxy. Journal of Applied Physics, 2011, 110, .	1.1	12

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73	Influence of a GaN Cap Layer on the Morphology and the Physical Properties of Embedded Self-Organized InN Quantum Dots on GaN(0001) Grown by Metalâ€“Organic Vapour Phase Epitaxy. Japanese Journal of Applied Physics, 2011, 50, 031004.	0.8	8
74	Influence of a GaN Cap Layer on the Morphology and the Physical Properties of Embedded Self-Organized InN Quantum Dots on GaN(0001) Grown by Metalâ€“Organic Vapour Phase Epitaxy. Japanese Journal of Applied Physics, 2011, 50, 031004.	0.8	3
75	Growth of semipolar (10$ ar 1ar 3 $) InN on <i>m</i> â€plane sapphire using MOVPE. Physica Status Solidi - Rapid Research Letters, 2010, 4, 127-129.	1.2	14
76	Metalorganic vapor phase epitaxy of InN on GaN using tertiary-butylhydrazine as nitrogen source. Journal of Crystal Growth, 2010, 312, 1983-1985.	0.7	1
77	Orientation control of GaN and grown on sapphire by metal-organic vapor phase epitaxy. Journal of Crystal Growth, 2010, 312, 2171-2174.	0.7	42
78	Determination of the complex linear electroâ€optic coefficient of GaAs and InP. Physica Status Solidi (B): Basic Research, 2010, 247, 1974-1978.	0.7	4
79	Volmerâ€Weber growth mode of InN quantum dots on GaN by MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S545.	0.8	18
80	Growth mode of InGaN on GaN (0001) in MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S565-S569.	0.8	22
81	Shape of indium nitride quantum dots and nanostructures grown by metal organic vapour phase epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S574-S577.	0.8	3
82	Properties of InMnP (001) grown by MOVPE. Journal of Crystal Growth, 2008, 310, 4046-4049.	0.7	4
83	Ripening of InAs quantum dots on GaAs (001) investigated with in situ scanning tunneling microscopy in metalâ€“organic vapor phase epitaxy. Journal of Crystal Growth, 2008, 310, 4751-4753.	0.7	13
84	Indium nitride quantum dot growth modes in metalorganic vapour phase epitaxy. Journal of Crystal Growth, 2008, 310, 4959-4962.	0.7	10
85	Growth and characterization of manganese-doped InAsP. Journal of Crystal Growth, 2008, 310, 5028-5031.	0.7	0
86	The critical thickness of InGaN on (0001)GaN. Journal of Crystal Growth, 2008, 310, 4913-4915.	0.7	104
87	In-Situ Monitoring for Nano-Structure Growth inÂMOVPE. Nanoscience and Technology, 2008, , 67-86.	1.5	0
88	Homoepitaxial growth rate measurement using in situ reflectance anisotropy spectroscopy. Journal of Crystal Growth, 2007, 298, 46-49.	0.7	6
89	In situ scanning tunnelling microscopy during metal-organic vapour phase epitaxy. Journal of Crystal Growth, 2007, 298, 8-11.	0.7	7
90	Segregation and desorption of antimony in InP (001) in MOVPE. Journal of Crystal Growth, 2007, 298, 159-162.	0.7	8

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91	InN growth on sapphire using different nitridation procedures. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 1622-1625.	0.8	9
92	In situ scanning tunneling microscopy during metal-organic vapor phase epitaxy. Applied Physics Letters, 2006, 89, 063108.	1.5	6
93	Growth of strained GaAsSb layers on GaAs (001) by MOVPE. Journal of Crystal Growth, 2005, 276, 347-353.	0.7	26
94	Development of InN metalorganic vapor phase epitaxy using in-situ spectroscopic ellipsometry. Crystal Research and Technology, 2005, 40, 993-996.	0.6	3
95	A fast reflectance anisotropy spectrometer for in situ growth monitoring. Physica Status Solidi (B): Basic Research, 2005, 242, 2561-2569.	0.7	16
96	Structural analysis by reflectance anisotropy spectroscopy: As and Sb on GaAs(110). Journal of Physics Condensed Matter, 2004, 16, S4367-S4374.	0.7	4
97	Lateral short range ordering of step bunches in InGaAs/GaAs superlattices. Journal of Applied Physics, 2004, 95, 1736-1739.	1.1	3
98	In situ study of GaAs growth mechanisms using tri-methyl gallium and tri-ethyl gallium precursors in metal-organic vapour phase epitaxy. Journal of Crystal Growth, 2004, 262, 78-83.	0.7	25
99	InN growth and annealing investigations using in-situ spectroscopic ellipsometry. Journal of Crystal Growth, 2004, 272, 87-93.	0.7	14
100	In situ study of low-temperature growth and Mn, Si, Sn doping of GaAs () in molecular beam epitaxy. Journal of Crystal Growth, 2004, 265, 425-433.	0.7	2
101	Nitrogenâ€“arsenic exchange processes and investigation of the nitrided GaAs surfaces in MOVPE. Journal of Crystal Growth, 2004, 272, 30-36.	0.7	4
102	Ga-rich GaAs(001) surfaces observed by STM during high-temperature annealing in MBE. Journal of Crystal Growth, 2003, 251, 46-50.	0.7	17
103	In situ scanning tunneling microscopy of InAs quantum dots on GaAs() during molecular beam epitaxial growth. Surface Science, 2003, 544, 234-240.	0.8	14
104	Structure of Ga-stabilized GaAs(0 0 1) surfaces at high temperatures. Applied Surface Science, 2003, 212-213, 146-150.	3.1	5
105	Gallium-rich reconstructions on GaAs(001). Physica Status Solidi (B): Basic Research, 2003, 240, 91-98.	0.7	27
106	Influence of the reconstruction of GaAs (001) on the electro-optical bulk properties. Journal of Crystal Growth, 2003, 248, 254-258.	0.7	12
107	Structure analysis of the Ga-stabilizedGaAs(001)â˜c(8Ã—2)surface at high temperatures. Physical Review B, 2002, 65, .	1.1	28
108	Novel Organopalladium Material Formed on a Sulfur-Terminated GaAs(001) Surface. Japanese Journal of Applied Physics, 2002, 41, L1197-L1199.	0.8	17

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109	Real-time calibration of wafer temperature, growth rate and composition by optical in-situ techniques during AlxGa1â^’xAs growth in MOVPE. Journal of Crystal Growth, 2002, 240, 87-97.	0.7	28
110	In-situ Determination of the Carrier Concentration of (001) GaAs by Reflectance Anisotropy Spectroscopy. Physica Status Solidi A, 2001, 188, 1423-1429.	1.7	21
111	In situ investigation of GaAs (001) intrinsic carbon p-doping in metal-organic vapour phase epitaxy. Journal of Crystal Growth, 2000, 221, 149-155.	0.7	21
112	Diffusion of Ga on the GaAs (113) surface in the [11ì„0] direction during MOVPE growth. Applied Surface Science, 2000, 166, 433-436.	3.1	6
113	Atomic structure and composition of the (2Ã—4) reconstruction of InGaP(001). Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 2210.	1.6	7
114	Surface structure of ordered InGaP(001): The(2Ã—4)reconstruction. Physical Review B, 2000, 62, 12601-12604.	1.1	23
115	Dynamic study of the surfaces of (001) gallium arsenide in metal-organic vapor-phase epitaxy during arsenic desorption. Journal of Applied Physics, 2000, 87, 1245-1250.	1.1	14
116	GaP(001) and InP(001): Reflectance anisotropy and surface geometry. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 1691.	1.6	50
117	(2Ã—4)GaP(001) surface: Atomic structure and optical anisotropy. Physical Review B, 1999, 60, 2488-2494.	1.1	58
118	Comparative study of the GaAs (113), (115), (001), (115) , (113) , and (110) surfaces by atomic force microscopy, low energy electron diffraction, and reflectance anisotropy spectroscopy. Microelectronics Journal, 1999, 30, 449-453.	1.1	9
119	Spectroscopic process sensors in MOVPE device production. Applied Physics A: Materials Science and Processing, 1999, 68, 309-313.	1.1	32
120	Real-time monitoring of MOVPE device growth by reflectance anisotropy spectroscopy and related optical techniques. Journal of Crystal Growth, 1998, 195, 151-162.	0.7	54
121	Reconstructions of the GaAs (113) surface. Journal of Crystal Growth, 1998, 195, 1-5.	0.7	14
122	In situ characterization of GaAs growth in nitrogen atmosphere during MOVPE: a comparison to hydrogen atmosphere. Journal of Crystal Growth, 1998, 195, 211-216.	0.7	30
123	Response of the surface dielectric function to dynamic surface modifications: application of reflectance anisotropy spectroscopy and spectroscopic ellipsometry. Thin Solid Films, 1998, 313-314, 537-543.	0.8	9
124	Ellipsometric and reflectance-anisotropy measurements on rotating samples. Thin Solid Films, 1998, 313-314, 620-624.	0.8	24
125	Photoluminescence Scanning Near-Field Optical Microscopy on IIIâ€"V Quantum Dots. Physica Status Solidi A, 1998, 170, 401-410.	1.7	4
126	Atomic structure of InP(001)-(2Ã—4): A dimer reconstruction. Physical Review B, 1998, 57, 14596-14599.	1.1	64

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127	Optical anisotropies of InP(001) surfaces. Journal of Applied Physics, 1997, 81, 3611-3615.	1.1	17
128	Structure of InP (001) surfaces prepared by decapping and by ion bombardment and annealing. Physical Review B, 1997, 56, R1661-R1663.	1.1	18
129	In situ surface passivation of IIIâ€“V semiconductors in MOVPE by amorphous As and P layers. Journal of Crystal Growth, 1997, 170, 230-236.	0.7	24
130	Scanning-tunneling-microscopy study of InP(001) surfaces prepared by UHV decapping of metal-organic vapor-phase-epitaxy-grown samples. Physical Review B, 1996, 53, R13257-R13259.	1.1	37
131	Reflectance anisotropy oscillations during MOCVD and MBE growth of GaAs (001). Physica Status Solidi A, 1995, 152, 35-47.	1.7	43
132	Metalorganic vapour phase epitaxial growth on vicinal GaAs (001) surfaces studied by reflectance anisotropy spectroscopy. Physica Status Solidi A, 1995, 152, 49-59.	1.7	21
133	Growth oscillations with monolayer periodicity monitored by ellipsometry during metalorganic vapor phase epitaxy of GaAs(001). Applied Physics Letters, 1995, 67, 3783-3785.	1.5	41
134	Efficiency of arsenic and phosphorus precursors investigated by reflectance anisotropy spectroscopy. Journal of Crystal Growth, 1994, 145, 36-43.	0.7	19
135	Surface processes before and during growth of GaAs (001). Journal of Crystal Growth, 1994, 145, 44-52.	0.7	42